

Features

- $BV_{CEO} > -40V$
- $I_C = -200mA$ High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMDT3904
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

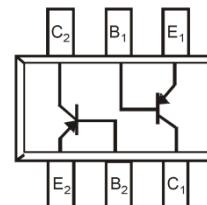
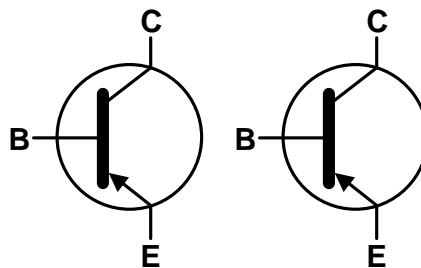
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)

SOT363



Top View


 Device Schematic
 Top View

Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT3906-7-F	Active	AEC-Q101	K3N	7	8	3,000

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

SOT363



K3N = Product Type Marking Code

YM = Date Code Marking

 Y or \bar{Y} = Year (ex: D = 2016)

 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	D	E	F	G	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 5. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristic and Derating Information

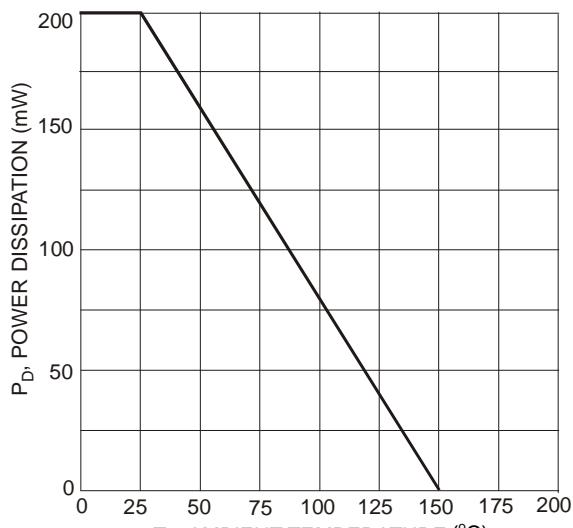


Fig. 1, Power Dissipation vs.
Ambient Temperature (Total Device)

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	$I_C = -10\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV_{CEO}	-40	—	V	$I_C = -1\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	$I_E = -10\mu\text{A}$, $I_C = 0$
Collector Cut-Off Current	I_{CEX}	—	-50	nA	$V_{\text{CE}} = -30\text{V}$, $V_{\text{EB}(\text{OFF})} = -3.0\text{V}$
Base Cut-Off Current	I_{BL}	—	-50	nA	$V_{\text{CE}} = -30\text{V}$, $V_{\text{EB}(\text{OFF})} = -3.0\text{V}$
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h_{FE}	60	—	—	$I_C = -100\mu\text{A}$, $V_{\text{CE}} = -1\text{V}$
		80	—	—	$I_C = -1.0\text{mA}$, $V_{\text{CE}} = -1\text{V}$
		100	300	—	$I_C = -10\text{mA}$, $V_{\text{CE}} = -1\text{V}$
		60	—	—	$I_C = -50\text{mA}$, $V_{\text{CE}} = -1\text{V}$
		30	—	—	$I_C = -100\text{mA}$, $V_{\text{CE}} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{\text{CE}(\text{SAT})}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$ $I_C = -50\text{mA}$, $I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{\text{BE}(\text{SAT})}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$ $I_C = -50\text{mA}$, $I_B = -5\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	—	4.5	pF	$V_{\text{CB}} = -5.0\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$
Input Capacitance	C_{IBO}	—	10	pF	$V_{\text{EB}} = -0.5\text{V}$, $f = 1.0\text{MHz}$, $I_C = 0$
Input Impedance	h_{ie}	2	12	k Ω	$V_{\text{CE}} = -10\text{V}$, $I_C = -1.0\text{mA}$, $f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	3	60	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	$V_{\text{CE}} = -20\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$
Noise Figure	N_F	—	4.0	dB	$V_{\text{CE}} = -5.0\text{V}$, $I_C = -100\mu\text{A}$, $R_S = 1.0\text{k}\Omega$, $f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_D	—	35	ns	$V_{\text{CC}} = -3.0\text{V}$, $I_C = -10\text{mA}$, $I_{B1} = I_{B2} = -1.0\text{mA}$
Rise Time	t_R	—	35	ns	
Storage Time	t_S	—	200	ns	
Fall Time	t_F	—	50	ns	

Note: 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

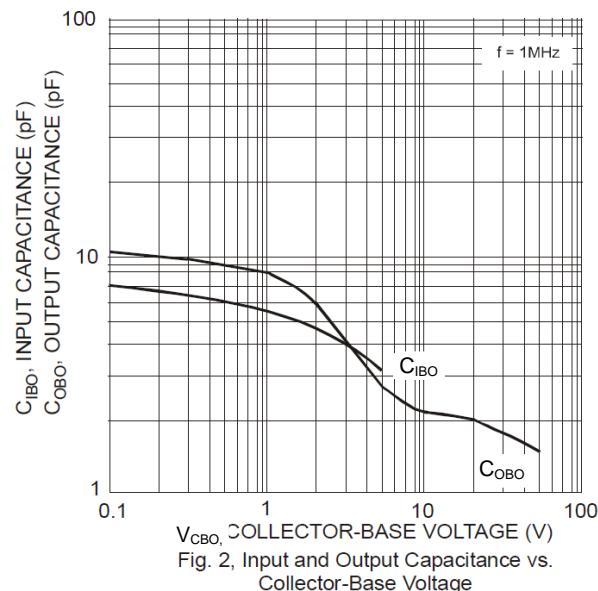


Fig. 2, Input and Output Capacitance vs.
Collector-Base Voltage

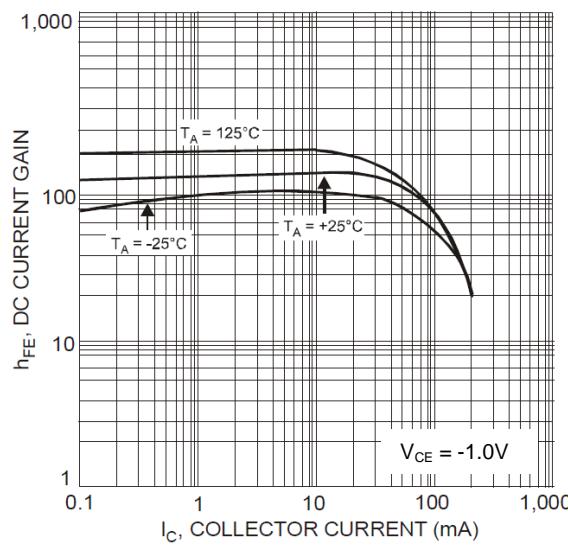


Fig. 3, Typical DC Current Gain vs.
Collector Current

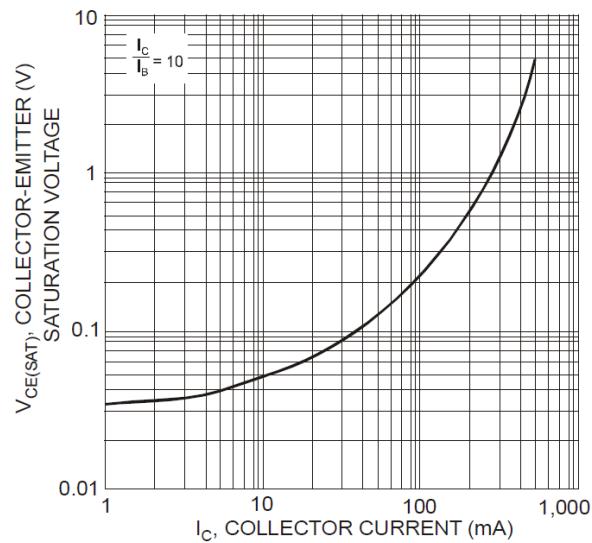


Fig. 4, Typical Collector-Emitter Saturation Voltage
vs. Collector Current

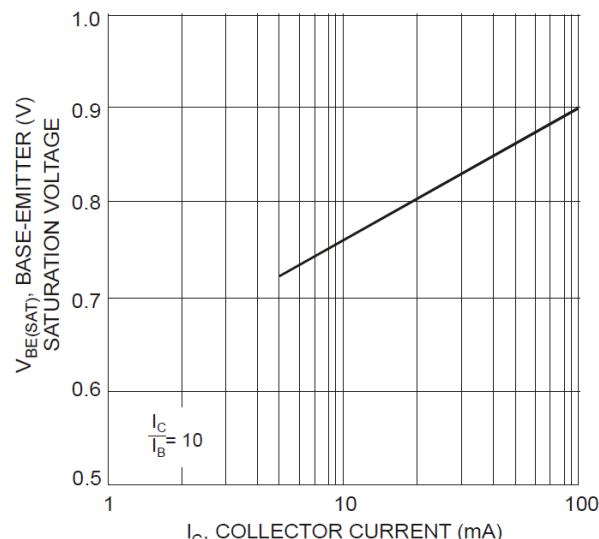
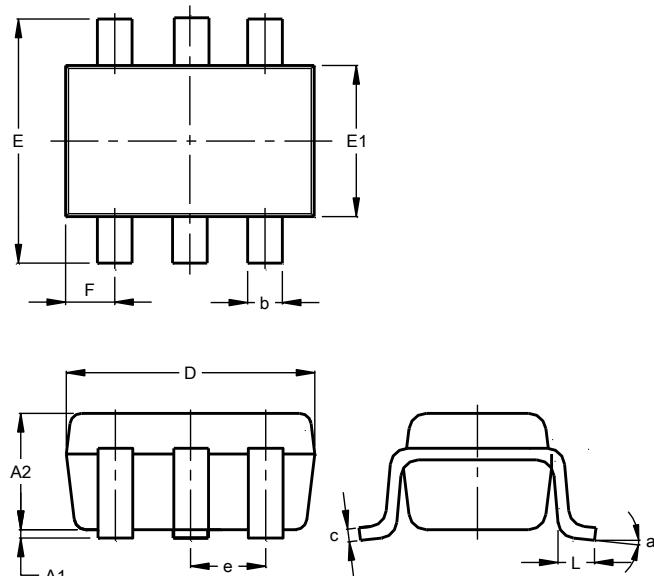


Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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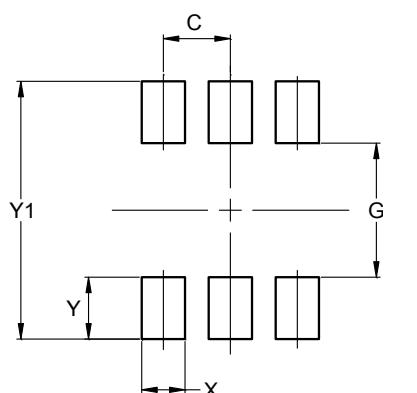
SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650	BSC	
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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